


MITSUBISHI IGBT  
**CY20AAJ-8F**

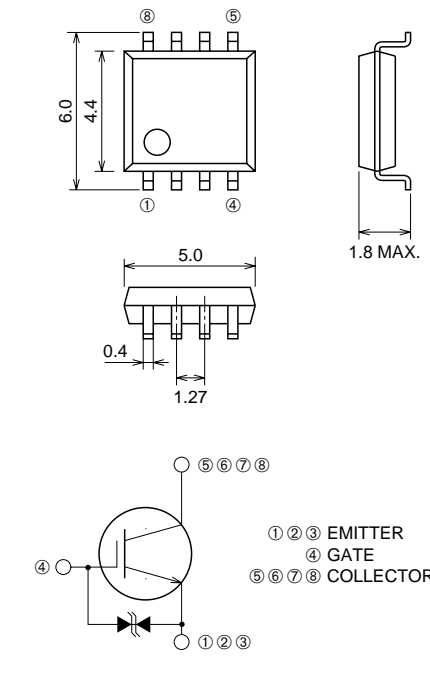
Nch IGBT for STROBE FLASHER

**CY20AAJ-8F**



- VCES ..... 400V
- ICM ..... 130A
- Drive voltage ..... 4V

**OUTLINE DRAWING** Dimensions in mm



**SOP-8**

**APPLICATION**

Strobe Flasher for camera

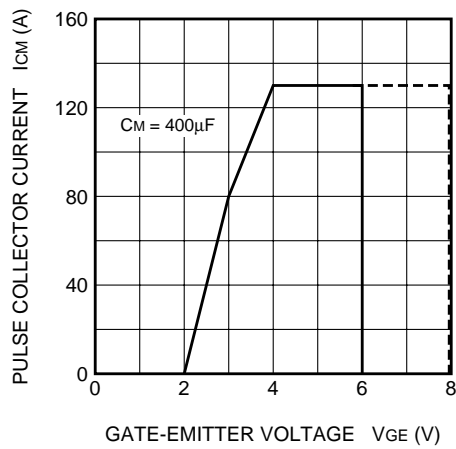
**MAXIMUM RATINGS** (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-emitter voltage	V <sub>GE</sub> = 0V	400	V
V <sub>GES</sub>	Gate-emitter voltage	V <sub>CE</sub> = 0V	±6	V
V <sub>GEM</sub>	Peak gate-emitter voltage	V <sub>CE</sub> = 0V, t <sub>w</sub> = 10s	±8	V
I <sub>CM</sub>	Collector current (Pulsed)	C <sub>M</sub> = 400μF see figure1	130	A
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +150	°C

**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub> = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	I <sub>C</sub> = 1mA, V <sub>GE</sub> = 0V	450	—	—	V
V (BR) GES	Gate-emitter breakdown voltage	I <sub>G</sub> = ±100μA, V <sub>CE</sub> = 0V	±8	—	—	V
I <sub>CES</sub>	Collector-emitter leakage current	V <sub>CE</sub> = 400V, V <sub>GE</sub> = 0V	—	—	10	μA
I <sub>GES</sub>	Gate-emitter leakage current	V <sub>GE</sub> = ±6V, V <sub>CE</sub> = 0V	—	—	±10	μA
V <sub>GE</sub> (th)	Gate-emitter threshold voltage	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA	—	—	1.5	V

**Figure1. MAXIMUM PULSE COLLECTOR CURRENT**



**APPLICATION EXAMPLE**

